

Large-Scale Atomistic Simulations of Materials using SNAP Potentials



Aidan Thompson

Mitchell Wood

Mary Alice Cusentino

Center for Computing Research, Sandia National Laboratories

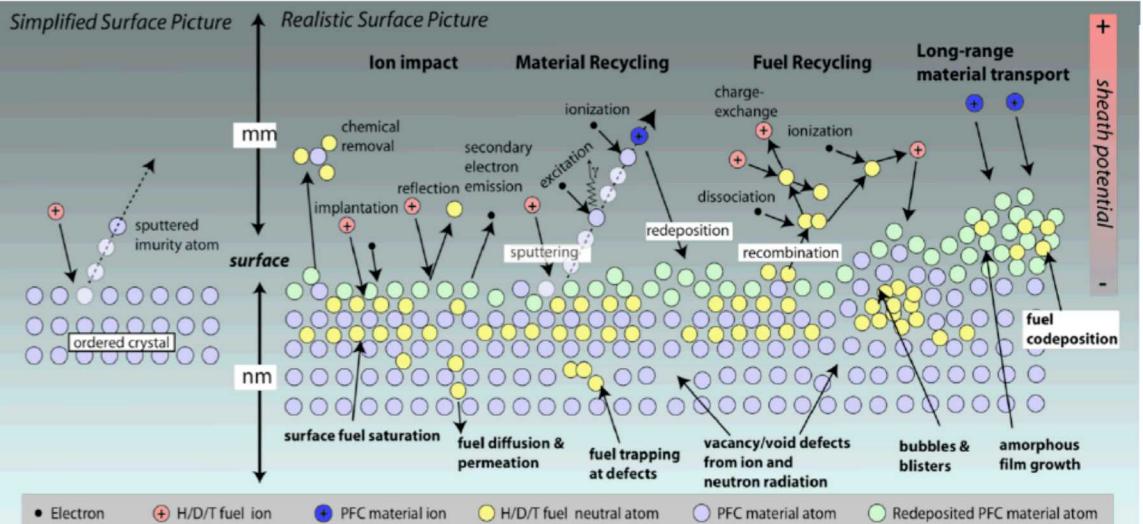
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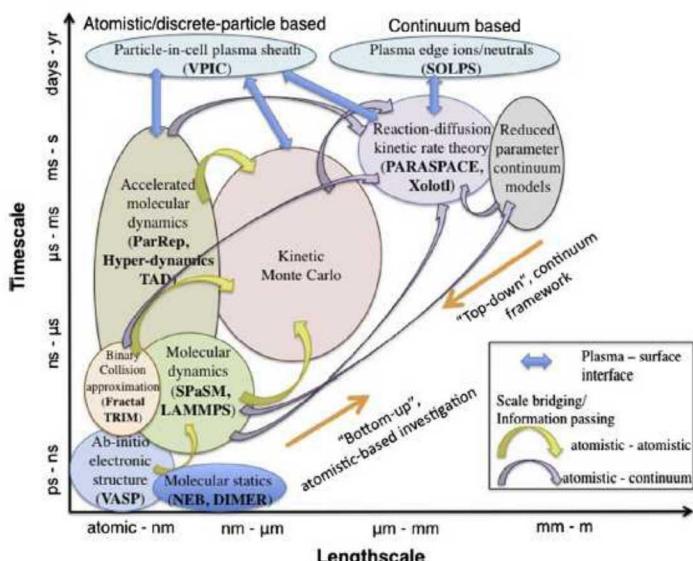


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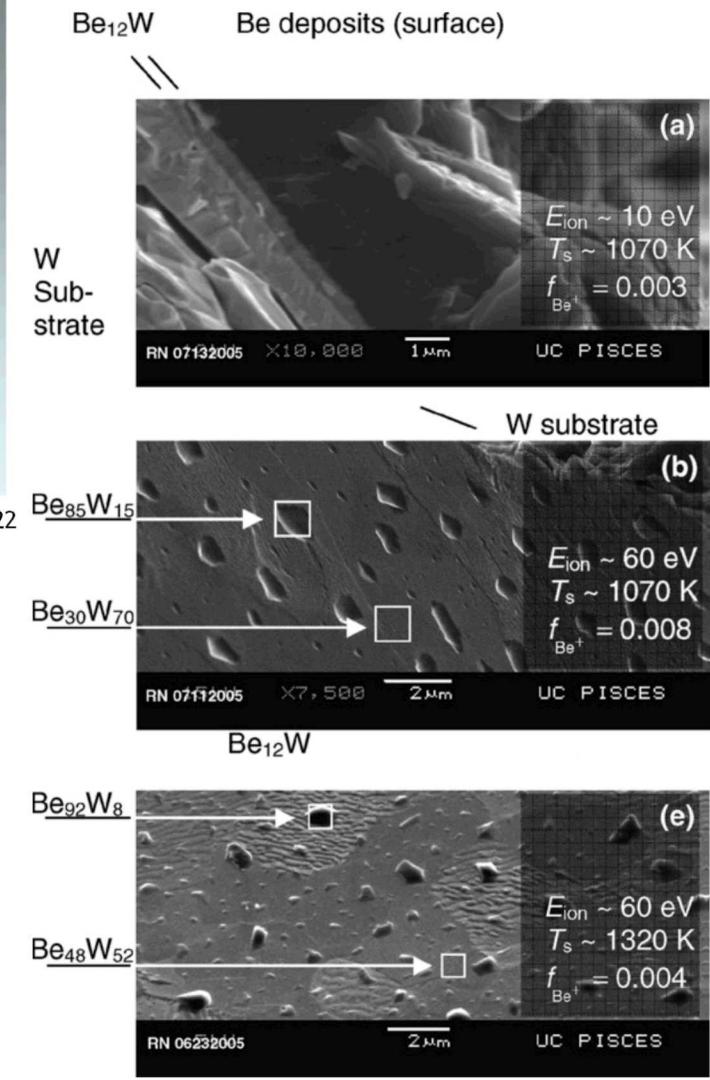
Role of Atomistic Modeling in Studying Plasma Material Interactions



Wirth, et al. MRS Bulletin 36 (2011) 216-222



Wirth, et. al. J. Nucl. Mater. 463 (2015) 30-38



Baldwin, et. al. J. Nucl. Mater. 363-365 (2007) 1179-1183



Model Form

- Energy of atom i expressed as a basis expansion over K components of the bispectrum (B_k^i)

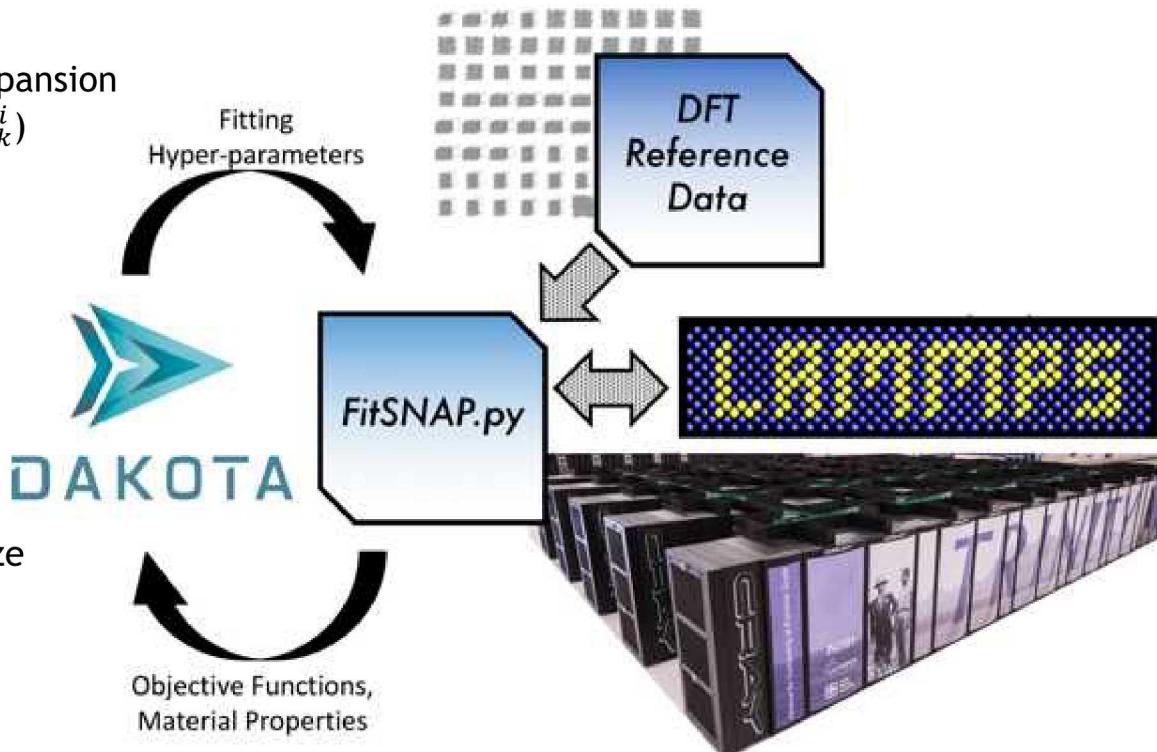
$$E_{SNAP}^i = \beta_0 + \sum_{k=1}^K \beta_k (B_k^i - B_{k0}^i)$$

Regression Method

- β vector fully describes a SNAP potential
- Decouples MD speed from training set size

$$\min(\|\mathbf{w} \cdot D\beta - T\|^2 - \gamma_n \|\beta\|^n)$$

Weights Set of Descriptors DFT Training

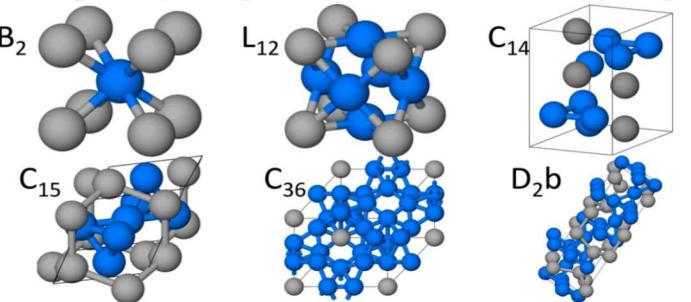
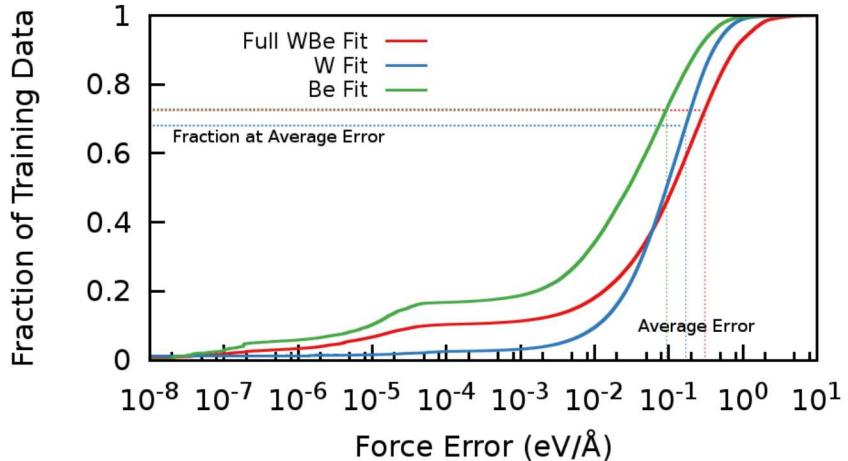
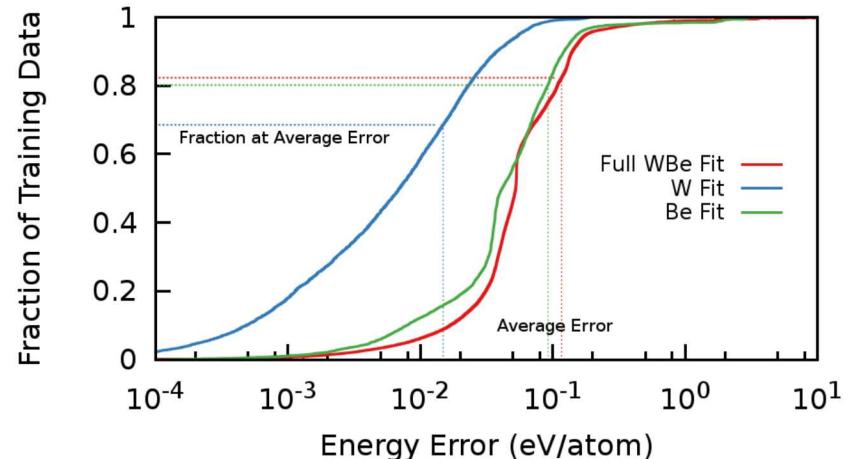


Tungsten-Beryllium SNAP Fitting

- Initially fit SNAP potential for pure elements
- Making a multi-element SNAP potential does sacrifice some accuracy from either pure component fit.
- Training set includes W-Be intermetallic structures

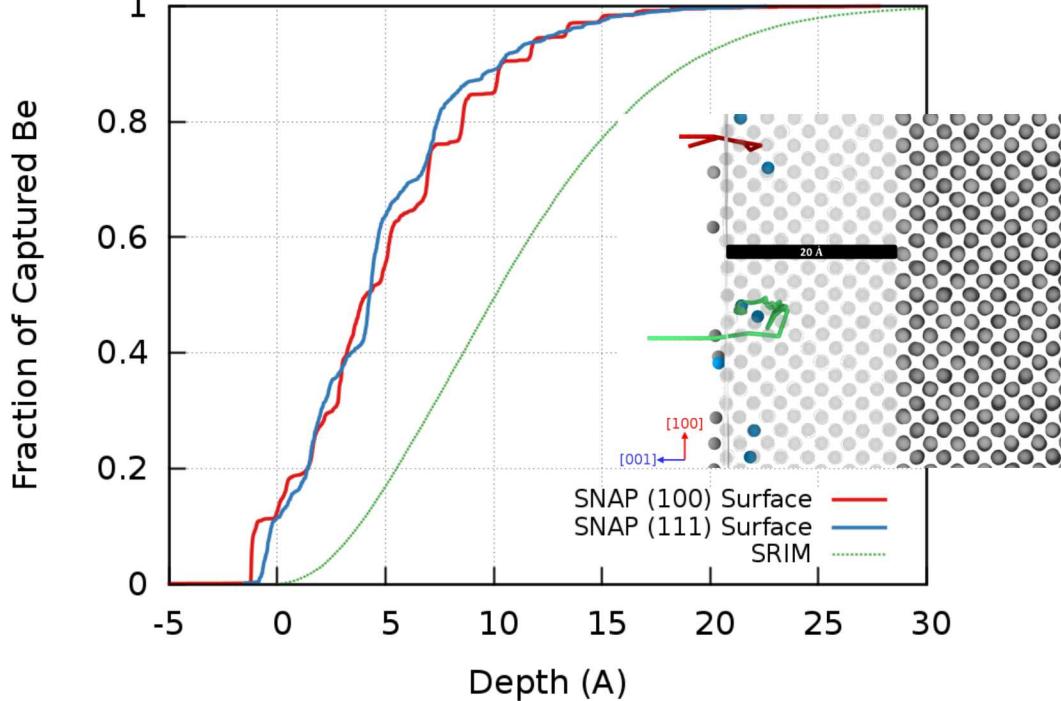
Description	N_E	N_F	σ_E	σ_F
W-Be:				
Elastic Deform [†]	3946	68040	$3 \cdot 10^5$	$2 \cdot 10^3$
Equation of State [†]	1113	39627	$2 \cdot 10^5$	$4 \cdot 10^4$
DFT-MD [†]	3360	497124	$7 \cdot 10^4$	$6 \cdot 10^2$
Surface Adhesion	381	112527	$2 \cdot 10^4$	$9 \cdot 10^4$

† Multiple crystal phases included in this group:

Extrapolation Testing – Single Implantation Simulations

- Single implantations of 75 eV Be in W
- MD depth profile is more shallow than binary collision models predict
- Capture rate is lower than BC model at 40% (versus 60%)
- Improvement in defect formation energies



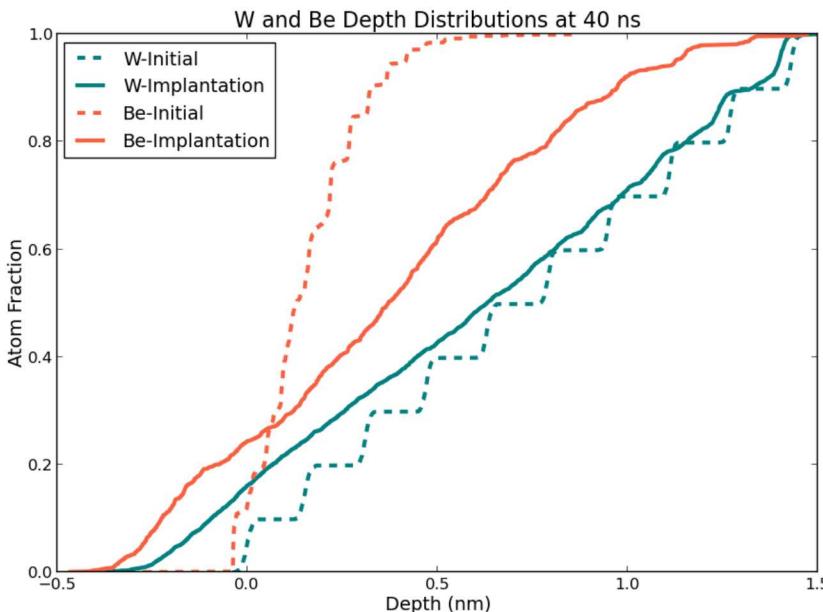
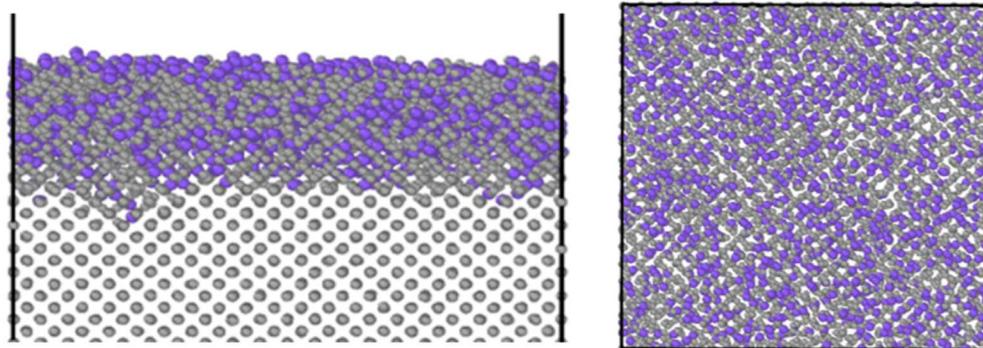
Defect Type	Percent of Implanted Be	
	(100) Surface	(111) Surface
[111] Dumbbell	41.2	23.9
Substitution	22.2	34.6
[100] Surf. Hollow Site	12.3	8.3
Tetrahedral Interstitial	10.4	12.4
[110] Dumbbell	8.4	11.3
Octahedral Interstitial	5.3	4.1
Other	0.4	2.8
Surf. Bridge Site	0.03	2.6

Defect Type	Formation Energy (eV)		
	DFT	SNAP	BOP
[111] Dumbbell	4.30	3.66	0.67
Substitution	3.11	3.29	-2.00
[100] Surf. Hollow Site	-1.05	-1.39	-3.52
Tetrahedral Interstitial	4.13	4.20	-0.28
[110] Dumbbell	4.86	4.29	-0.03
Octahedral Interstitial	3.00	5.11	0.34
[100] Surf. Bridge Site	1.01	0.44	-1.30

Cumulative Energetic Be Implantation in W

4000 inserted Be atoms, $1.1 \times 10^{20} \text{ m}^{-2}$
35% Retention

Purple: Beryllium
Gray: Tungsten

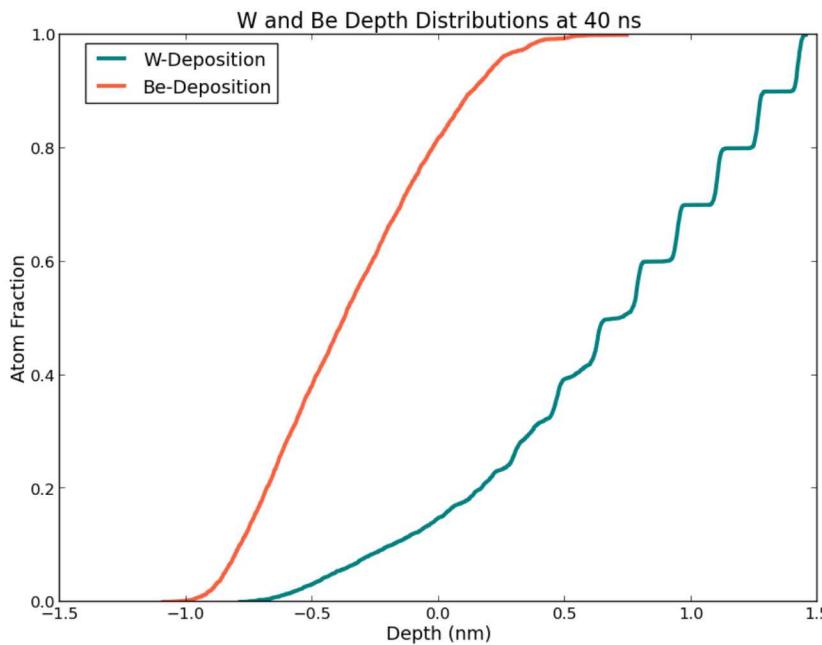
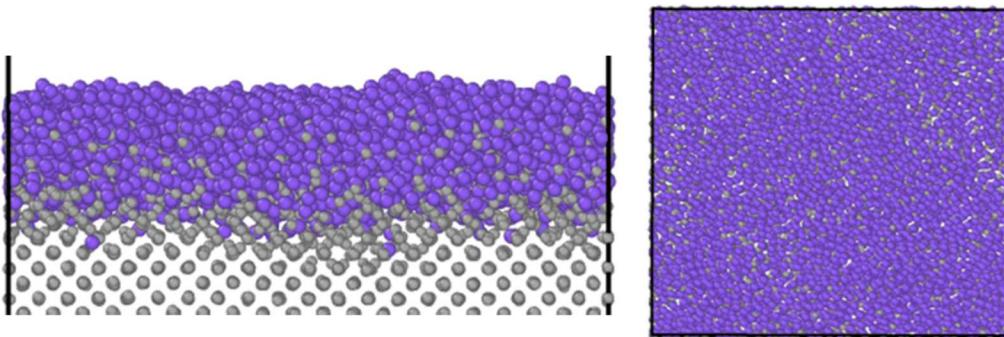


- 75 eV Be implanted every 10 ps
- 1000 K, (100) surface, 6 nm x 6 nm x 12 nm box
- Initially Be implants and resides in W as $<111>$ dumbbell or substitutional defects
- Amorphous layer forms 1.5 nm into surface and 0.3 nm above surface
- W depth profile indicates loss of crystal structure at higher fluences
- Be depth profile is deeper than expected based on initial implantation depth

Cumulative Be Athermal Deposition on W Surface

4000 inserted Be atoms, $1.1 \times 10^{20} \text{ m}^{-2}$

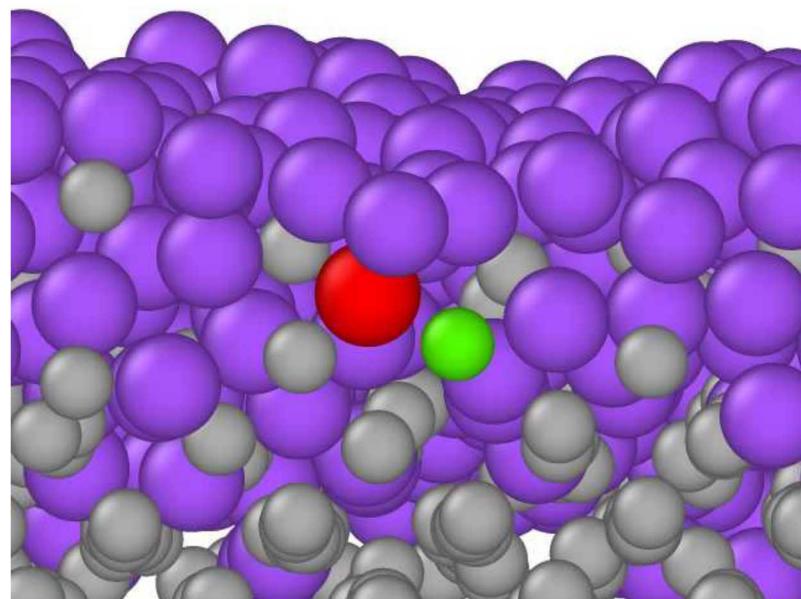
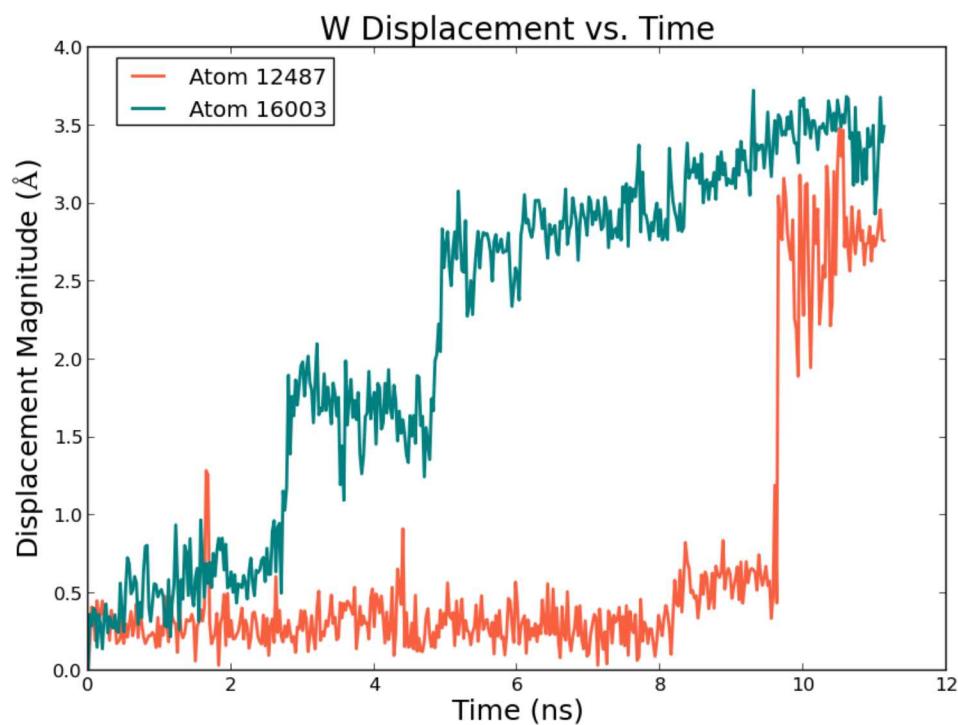
Purple: Beryllium
Gray: Tungsten



- Be randomly placed on surface every 10 ps with zero energy
- Initially Be resides at hollow sites
- Be begins to exchange with tungsten once hollow sites fill up
- Similar amorphous layer forms at higher fluences
- Thicker layer that extends from 0.5 nm below surface to 1 nm above surface
- Be remains near surface
- Almost 20% of W in the first 1.5 nm is now located above the original surface

Exchange Mechanism with Beryllium

Red: Be Exchanged
Green: W Exchanged
Purple: Be
Gray: W



- Clear jumps in tungsten displacement are exchanges with beryllium
- Low tungsten diffusion outside beryllium exchanges

Summary

- We have developed a machine learned SNAP potential for studying W-Be plasma material interactions
- The SNAP potential well reproduces both W and Be as well as W-Be intermetallic properties and improves upon existing potentials for parameters most relevant to radiation damage modeling
- We have performed large simulations of cumulative Be implantation or deposition on tungsten
- An amorphous layer of mixed W-Be has been observed which may be a precursor to intermetallic formation
- An exchange mechanism allows tungsten to migrate into the surface amorphous layer
- This potential will be extending to include both hydrogen and helium